


## Silicon Tuning Varactor

**BBY 33**

- Tuning varactor in passivated Mesa technology (epitaxial design)

Type	Marking	Ordering Code	Pin Configuration	Package <sup>1)</sup>
BBY 33 BB-2	–	Q62702-B70	Cathode: black dot, heat sink 	C 1

### Maximum Ratings

Parameter	Symbol	Values	Unit
Reverse voltage	$V_R$	27	V
Forward current	$I_F$	200	mA
Junction temperature	$T_j$	175	°C
Storage temperature range	$T_{stg}$	– 55 ... + 150	
Operating temperature range	$T_{op}$	– 55 ... + 150	

<sup>1)</sup> For detailed information see chapter Package Outlines.

**Electrical Characteristics**at  $T_A = 25\text{ °C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Forward voltage $I_F = 200\text{ mA}$	$V_F$	–	–	1.1	V
Reverse current $V_R = 15\text{ V}$	$I_R$	–	–	5	nA
Diode capacitance $V_R = 0$	$C_T$	0.9	–	1.5	pF
Capacitance ratio $V_R = 0, V_R = 25\text{ V}$	$\frac{C_{T0}}{C_{T25}}$	–	3.0	–	–
Figure of merit $V_R = 4\text{ V}, f = 50\text{ MHz}$	$Q_{(\min)}$	4000	–	–	–